

30 V, 3 A NPN low VCEsat (BISS) transistor

11 September 2014

Product data sheet

### 1. General description

NPN low V<sub>CEsat</sub> Breakthrough In Small Signal (BISS) transistor, encapsulated in an ultra thin DFN2020D-3 (SOT1061D) leadless small Surface-Mounted Device (SMD) plastic package with medium power capability and visible and soldarable side pads.

PNP complement: PBSS5330PAS

### 2. Features and benefits

- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability  ${\sf I}_C$  and  ${\sf I}_{CM}$
- High collector current gain (h<sub>FE</sub>) at high I<sub>C</sub>
- High efficiency due to less heat generation
- High temperature applications up to 175 °C
- Reduced Printed-Circuit Board (PCB) area requirements
- Leadless small SMD plastic package with soldarable side pads
- Exposed heat sink for excellent thermal and electrical conductivity
- Suitable for Automatic Optical Inspection (AOI) of solder joint
- AEC-Q101 qualified

### 3. Applications

- Loadswitch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

### 4. Quick reference data

Table 1.     Quick reference data							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-	30	V
I <sub>C</sub>	collector current			-	-	3	А
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-	5	А
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = 3 A; $I_B$ = 300 mA; pulsed; $t_p \le 300$ μs; δ ≤ 0.02; $T_{amb}$ = 25 °C		-	75	100	mΩ



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# 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	3	3
2	E	emitter		1-
3	С	collector	1 2	sym021
			Transparent top view DFN2020D-3 (SOT1061D)	

# 6. Ordering information

Table 3.         Ordering information						
Type number	Package					
	Name	Description	Version			
PBSS4330PAS	DFN2020D-3	DFN2020D-3: plastic thermal enhanced ultra thin small outline package; no leads; 3 terminals; body $2 \times 2 \times 0.65$ mm	SOT1061D			

### 7. Marking

Table 4.   Marking codes	
Type number	Marking code
PBSS4330PAS	E1

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### 8. Limiting values

#### Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	50	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	30	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	6	V
I <sub>C</sub>	collector current			-	3	А
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	5	А
I <sub>B</sub>	base current			-	500	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	600	mW
			[2][3]	-	1.2	W
			[4]	-	1.5	W
			[5][6]	-	2.5	W
Tj	junction temperature			-	175	°C
T <sub>amb</sub>	ambient temperature			-55	175	°C
T <sub>stg</sub>	storage temperature			-65	175	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

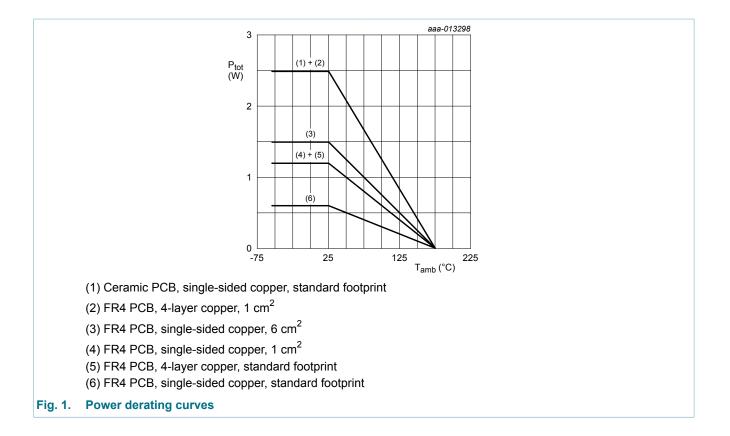
[3] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.

<sup>[4]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.

[5] Device mounted on a ceramic PCB,  $AI_2O_3$ , standard footprint.

<sup>[6]</sup> Device mounted on an FR4 PCB, 4-layer copper, tin-plated and mounting pad for collector 1 cm<sup>2</sup>.

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### 9. Thermal characteristics

Table 6. T	hermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub> thermal resistant from junction to ambient	thermal resistance	in free air	[1]	-	-	250	K/W
	-		[ <u>2][3]</u>	-	-	125	K/W
	ambient		[4]	-	-	100	K/W
			[5][6]	-	-	60	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

[3] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.

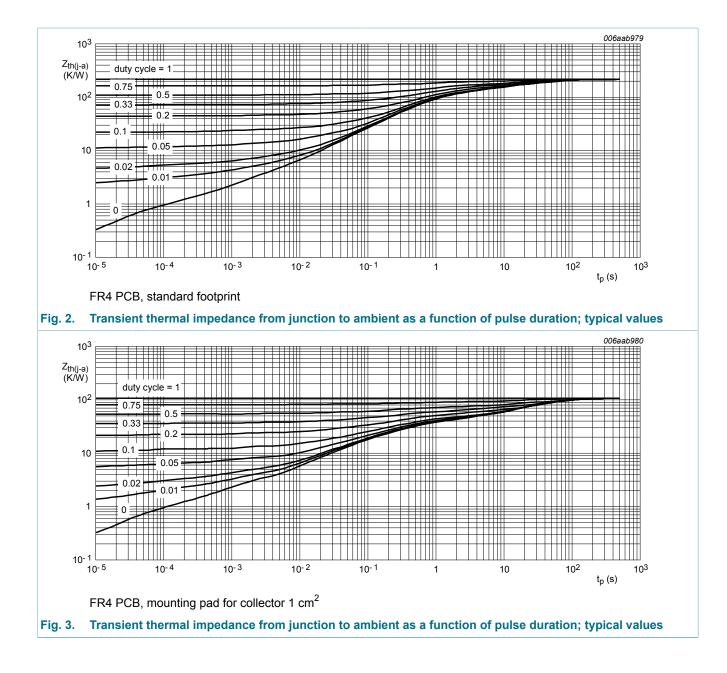
<sup>[4]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.

[5] Device mounted on a ceramic PCB,  $Al_2O_3$ , standard footprint.

<sup>[6]</sup> Device mounted on a FR4 PCB, 4-layer copper, tin-plated and mounting pad for collector 1 cm<sup>2</sup>.

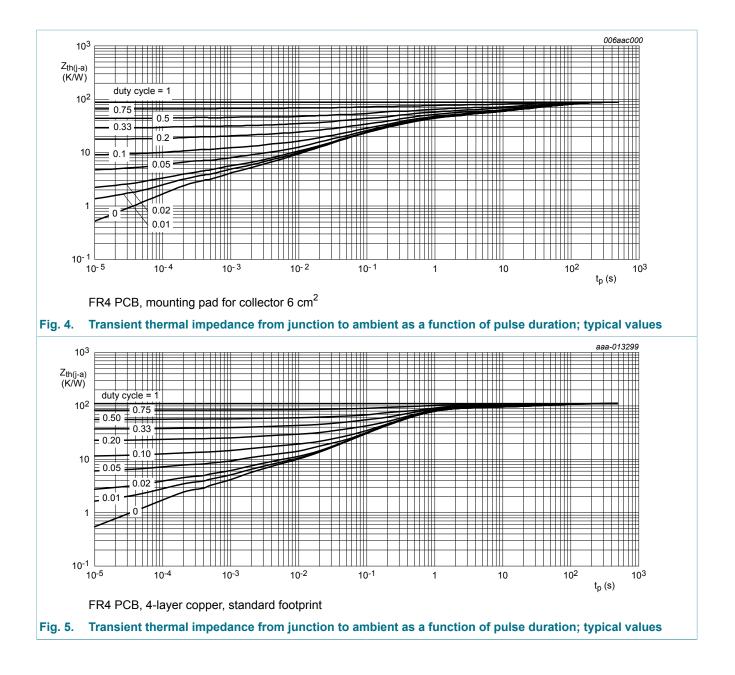


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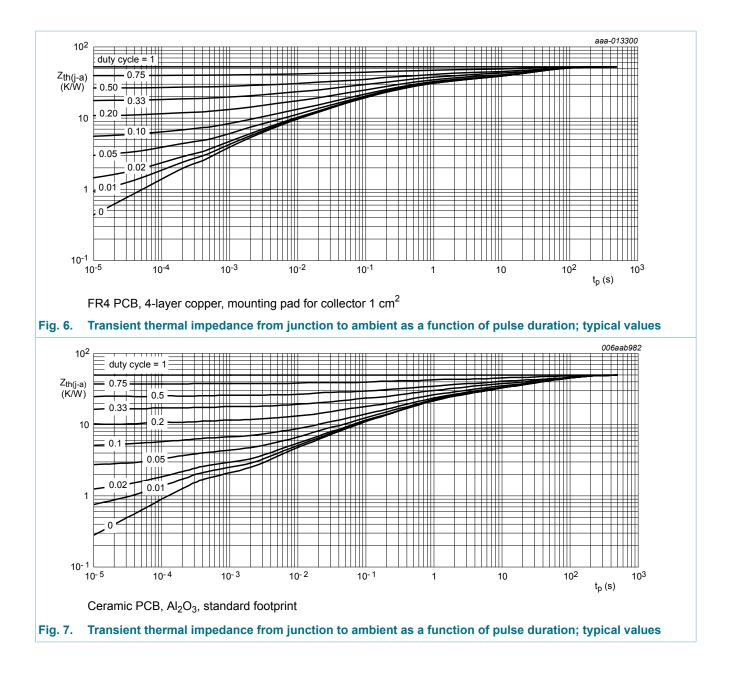
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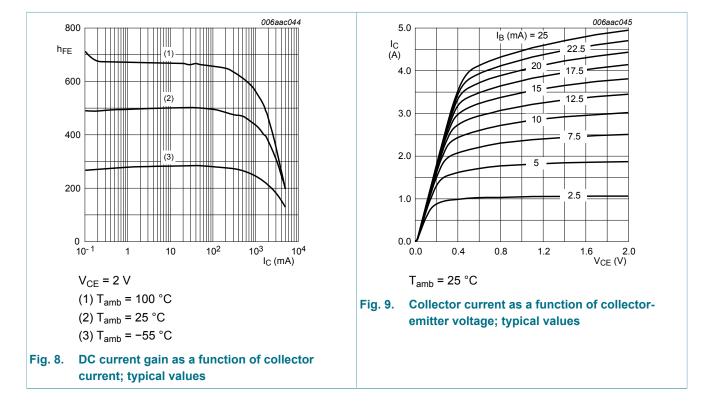
### **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	V <sub>CB</sub> = 24 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
	current	$V_{CB}$ = 24 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	50	μA
I <sub>CES</sub>	collector-emitter cut-off current	$V_{CE}$ = 24 V; $V_{BE}$ = 0 V; $T_{amb}$ = 25 °C	-	-	100	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB}$ = 5 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = 2 V; I <sub>C</sub> = 0.5 A; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	300	465	-	
		$V_{CE}$ = 2 V; I <sub>C</sub> = 1 A; pulsed; t <sub>p</sub> ≤ 300 µs; $\delta$ ≤ 0.02; T <sub>amb</sub> = 25 °C	270	435	700	
		$V_{CE}$ = 2 V; I <sub>C</sub> = 2 A; pulsed; t <sub>p</sub> ≤ 300 µs; $\delta$ ≤ 0.02; T <sub>amb</sub> = 25 °C	230	370	-	
		$V_{CE}$ = 2 V; I <sub>C</sub> = 3 A; pulsed; t <sub>p</sub> ≤ 300 µs; $\delta$ ≤ 0.02; T <sub>amb</sub> = 25 °C	180	310	-	
V <sub>CEsat</sub>	/ <sub>CEsat</sub> collector-emitter saturation voltage	$I_{C}$ = 0.5 A; $I_{B}$ = 50 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	40	60	mV
		$I_{C}$ = 1 A; $I_{B}$ = 50 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	80	110	mV
		$\begin{split} &I_{C} = 2 \; A; \; I_{B} = 100 \; mA; \; pulsed; \\ &t_{p} \leq 300 \; \mus; \; \delta \leq 0.02; \; T_{amb} = 25 \; ^{\circ}C \end{split}$	-	155	220	mV
		$I_{C}$ = 3 A; $I_{B}$ = 300 mA; pulsed;	-	220	300	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$t_p \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb} = 25 \ ^\circ C$	-	75	100	mΩ
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_{C}$ = 2 A; $I_{B}$ = 100 mA; pulsed; $t_{p}$ ≤ 300 µs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	0.95	1.1	V
		$I_{C}$ = 3 A; $I_{B}$ = 300 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	1.07	1.2	V
V <sub>BEon</sub>	base-emitter turn-on voltage	$V_{CE}$ = 2 V; I <sub>C</sub> = 1 A; pulsed; t <sub>p</sub> ≤ 300 µs; $\delta$ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	0.76	1	V
t <sub>d</sub>	delay time	V <sub>CC</sub> = 9 V; I <sub>C</sub> = 2 A; I <sub>Bon</sub> = 0.1 A;	-	11	-	ns
t <sub>r</sub>	rise time	I <sub>Boff</sub> = -0.1 A; T <sub>amb</sub> = 25 °C	-	52	-	ns
t <sub>on</sub>	turn-on time	-	-	63	-	ns
t <sub>s</sub>	storage time	-	-	230	-	ns
t <sub>f</sub>	fall time	-	-	40	-	ns
t <sub>off</sub>	turn-off time		-	270	-	ns

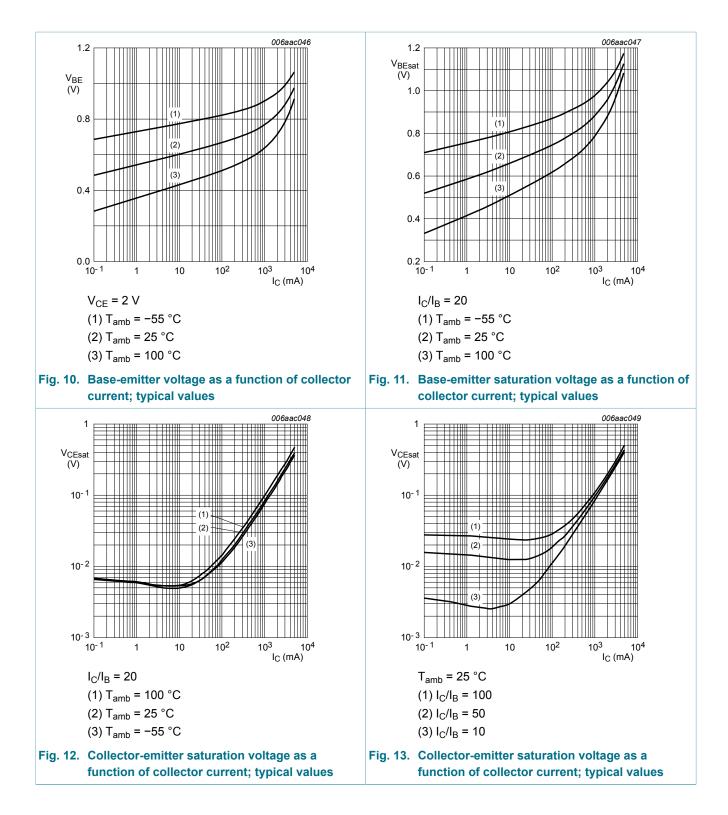
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f <sub>T</sub>	transition frequency	$V_{CE}$ = 5 V; I <sub>C</sub> = 100 mA; f = 100 MHz; T <sub>amb</sub> = 25 °C	100	210	-	MHz
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = 10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	21	30	pF



#### 30 V, 3 A NPN low VCEsat (BISS) transistor



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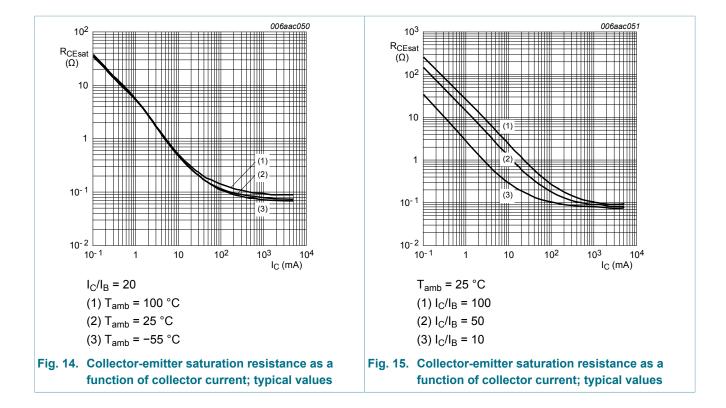
**Product data sheet** 

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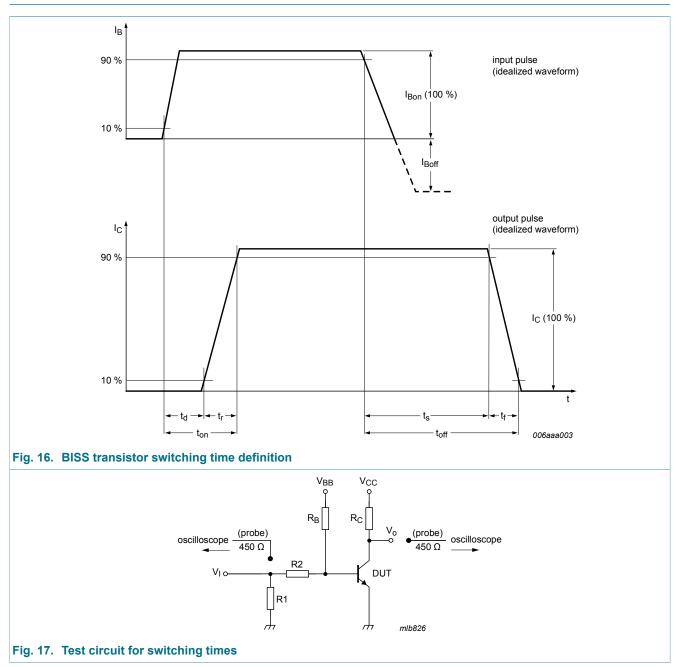
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### **11. Test information**

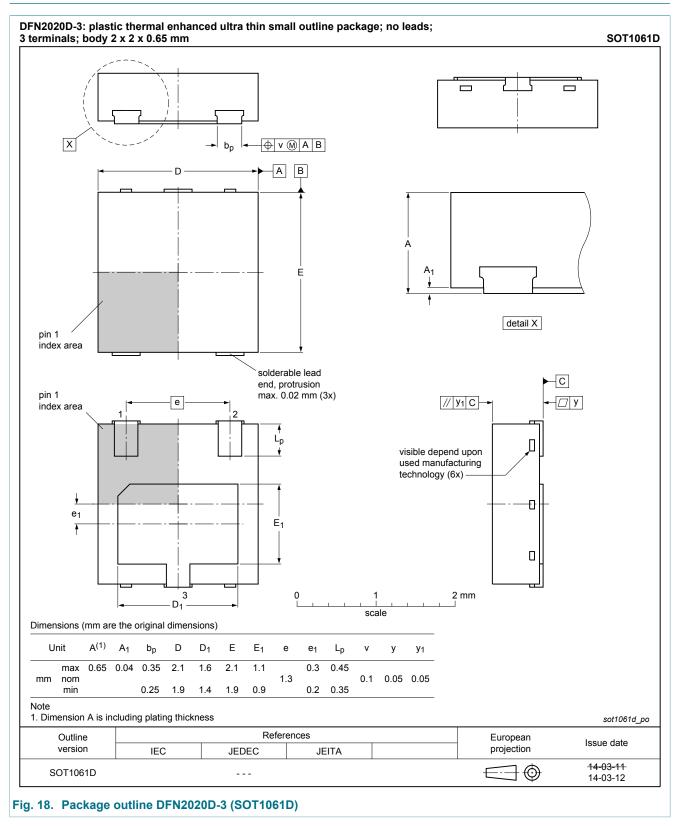
**11.1 Quality information** 

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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#### 30 V, 3 A NPN low VCEsat (BISS) transistor

### 12. Package outline

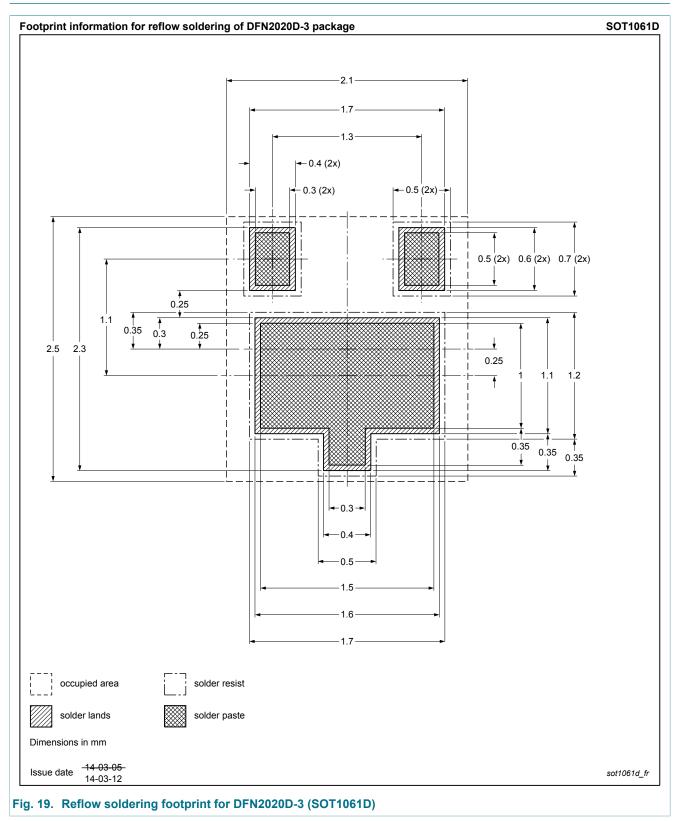


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### 13. Soldering



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# 14. Revision history

Table 8. Revision history						
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PBSS4330PAS v.1	20140911	Product data sheet	-	-		

#### 30 V, 3 A NPN low VCEsat (BISS) transistor

### 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

 Please consult the most recently issued document before initiating or completing a design.

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